

SuperMOS –SOT-23 60V  $BV_{DSS}$ ,  $1.8\Omega R_{DS(ON)}$ , N-channel MOSFET

## 1. Description

The BSS138BK is N-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product BSS138BK is Pb-free.

## 2. Features

- 60V,  $R_{DS(ON)}=1.8\Omega(\text{Typ.}) @V_{GS}=10V$   
 $R_{DS(ON)}=2.0\Omega(\text{Typ.}) @V_{GS}=4.5V$
- Use trench MOSFET technology
- High density cell design for low  $R_{DS(on)}$
- Material: Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current
- ESD Protection - HBM : 2kV

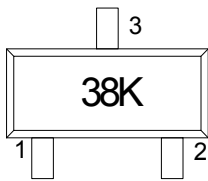
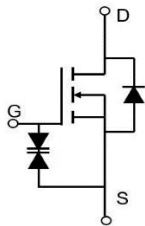
## 3. Applications

- PWM applications
- Load switch
- Power management in portable/desktop PCs
- DC/DC conversion

## 4. Ordering Information

| Part Number | Package | Marking | Material     | Packing     | Quantity per Reel | Flammability Rating | Reel Sizes |
|-------------|---------|---------|--------------|-------------|-------------------|---------------------|------------|
| BSS138BK    | SOT-23  | 38K     | Halogen free | Tape & Reel | 3,000 PCS         | UL 94V-0            | 7 inches   |

## 5. Pin Configuration and Functions

| Pin | Function | Outline                                                                             | Circuit Diagram                                                                       |
|-----|----------|-------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------|
| 1   | Gate     |  |  |
| 2   | Source   |                                                                                     |                                                                                       |
| 3   | Drain    |                                                                                     |                                                                                       |

## 6. Specification

### Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

| Parameter                      |                           | Symbol     | Limit      | Unit |
|--------------------------------|---------------------------|------------|------------|------|
| Drain-Source Voltage           |                           | $BV_{DSS}$ | 60         | V    |
| Gate-Source Voltage            |                           | $V_{GS}$   | ±20        | V    |
| Continuous Drain Current       | $T_A=25^{\circ}\text{C}$  | $I_D$      | 0.3        | A    |
|                                | $T_A=100^{\circ}\text{C}$ |            | 0.2        |      |
| Maximum Power Dissipation      |                           | $P_D$      | 0.35       | W    |
| Pulsed Drain Current           |                           | $I_{DM}$   | 1.2        | A    |
| Operating Junction Temperature |                           | $T_J$      | 150        | °C   |
| Lead Temperature               |                           | $T_L$      | 260        | °C   |
| Storage Temperature Range      |                           | $T_{stg}$  | -55 to 150 | °C   |

### Thermal resistance ratings

| Single Operation                                               |                 |         |         |      |
|----------------------------------------------------------------|-----------------|---------|---------|------|
| Parameter                                                      | Symbol          | Typical | Maximum | Unit |
| Junction-to-Ambient Thermal Resistance ( $t \leq 10\text{s}$ ) | $R_{\theta JA}$ |         | 357     | °C/W |

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## Electrical Characteristics

At TA = 25°C unless otherwise specified

| Parameter                                 | Symbol              | Test Conditions                                                                          | Min. | Typ. | Max. | Unit |
|-------------------------------------------|---------------------|------------------------------------------------------------------------------------------|------|------|------|------|
| OFF CHARACTERISTICS                       |                     |                                                                                          |      |      |      |      |
| Drain-to-Source Breakdown Voltage         | BV <sub>DSS</sub>   | V <sub>GS</sub> =0V, I <sub>D</sub> =250uA                                               | 60   |      |      | V    |
| Zero Gate Voltage Drain Current           | I <sub>DSS</sub>    | V <sub>DS</sub> =60V, V <sub>GS</sub> =0V                                                |      |      | 1    | uA   |
| Gate-to-source Leakage Current            | I <sub>GSS</sub>    | V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V                                               |      |      | ±10  | uA   |
| ON CHARACTERISTICS                        |                     |                                                                                          |      |      |      |      |
| Gate Threshold Voltage                    | V <sub>GS(TH)</sub> | V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA                                 | 0.7  | 1.1  | 1.5  | V    |
| Drain-to-source On-resistance             | R <sub>DS(on)</sub> | V <sub>GS</sub> =10V, I <sub>D</sub> =0.3A                                               |      | 1.8  | 2.2  | Ω    |
|                                           |                     | V <sub>GS</sub> =4.5V, I <sub>D</sub> =0.2A                                              |      | 2.0  | 3.0  |      |
| CHARGES, CAPACITANCES AND GATE RESISTANCE |                     |                                                                                          |      |      |      |      |
| Input Capacitance                         | C <sub>ISS</sub>    | V <sub>GS</sub> =0V, f=1MHz,<br>V <sub>DS</sub> =25V                                     |      | 15   |      | pF   |
| Output Capacitance                        | C <sub>OSS</sub>    |                                                                                          |      | 3.3  |      |      |
| Reverse Transfer Capacitance              | C <sub>RSS</sub>    |                                                                                          |      | 1.3  |      |      |
| Total Gate Charge                         | Q <sub>G(TOT)</sub> | V <sub>GS</sub> =4.5V, V <sub>DS</sub> =10V,<br>I <sub>D</sub> =0.3A                     |      | 1.6  |      | nC   |
| Gate-to-Source Charge                     | Q <sub>GS</sub>     |                                                                                          |      | 0.2  |      |      |
| Gate-to-Drain Charge                      | Q <sub>GD</sub>     |                                                                                          |      | 0.5  |      |      |
| SWITCHING CHARACTERISTICS                 |                     |                                                                                          |      |      |      |      |
| Turn-On Delay Time                        | t <sub>d(ON)</sub>  | V <sub>GS</sub> =10V, V <sub>DS</sub> =10V,<br>I <sub>D</sub> =0.2A, R <sub>G</sub> =10Ω |      | 2    |      | ns   |
| Rise Time                                 | t <sub>r</sub>      |                                                                                          |      | 14   |      |      |
| Turn-Off Delay Time                       | t <sub>d(OFF)</sub> |                                                                                          |      | 6    |      |      |
| Fall Time                                 | t <sub>f</sub>      |                                                                                          |      | 19   |      |      |
| BODY DIODE CHARACTERISTICS                |                     |                                                                                          |      |      |      |      |
| Forward Voltage                           | V <sub>SD</sub>     | V <sub>GS</sub> =0V, I <sub>S</sub> =0.3A                                                |      |      | 1.5  | V    |

7. Typical Characteristics

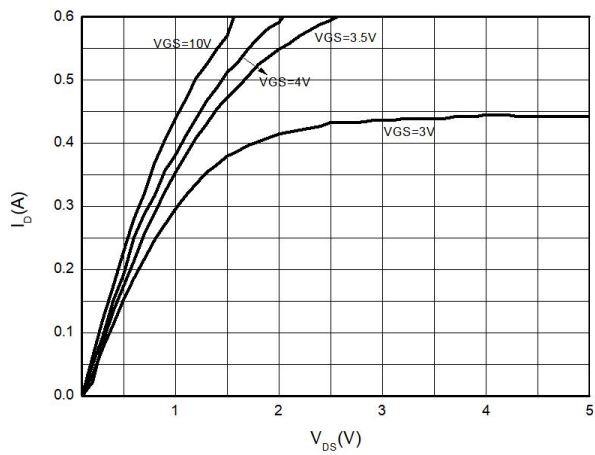


Figure1: Output Characteristics

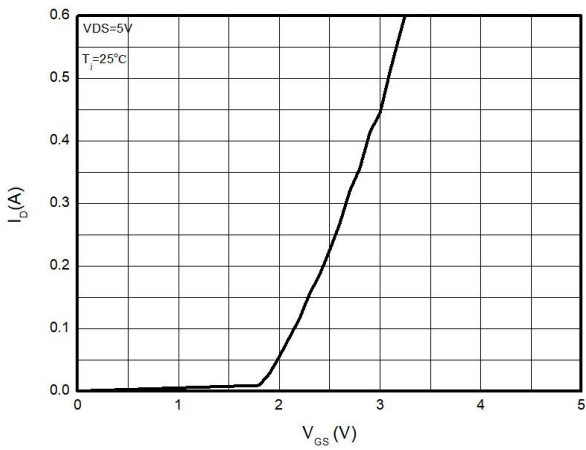


Figure2: Typical Transfer Characteristics

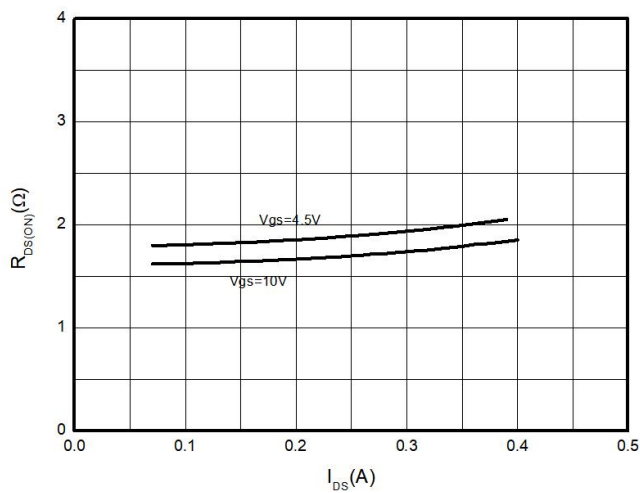


Figure3: on-Resistance vs. Drain Current

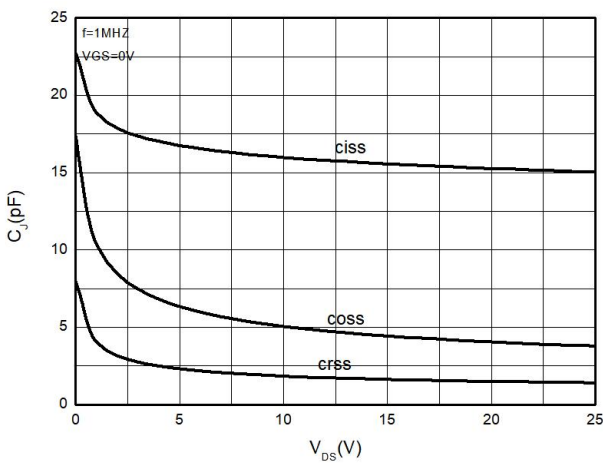


Figure4: Capacitance Characteristics

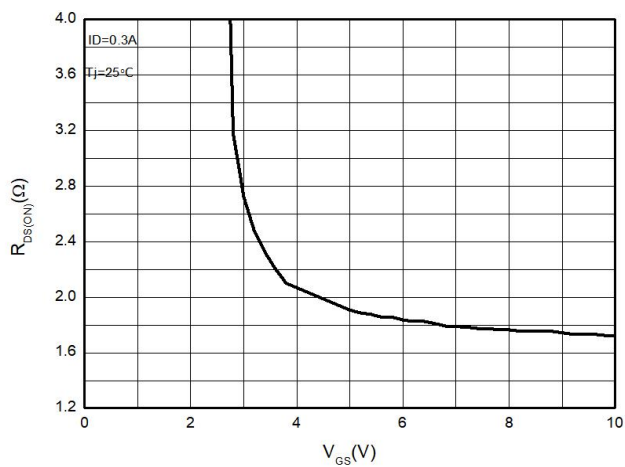


Figure5: on-Resistance vs. Gate to Source

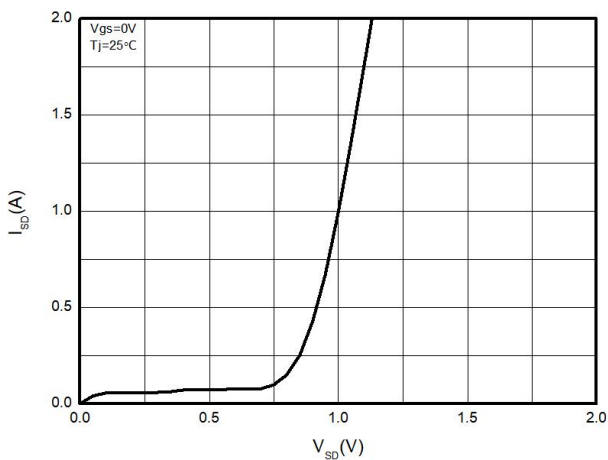
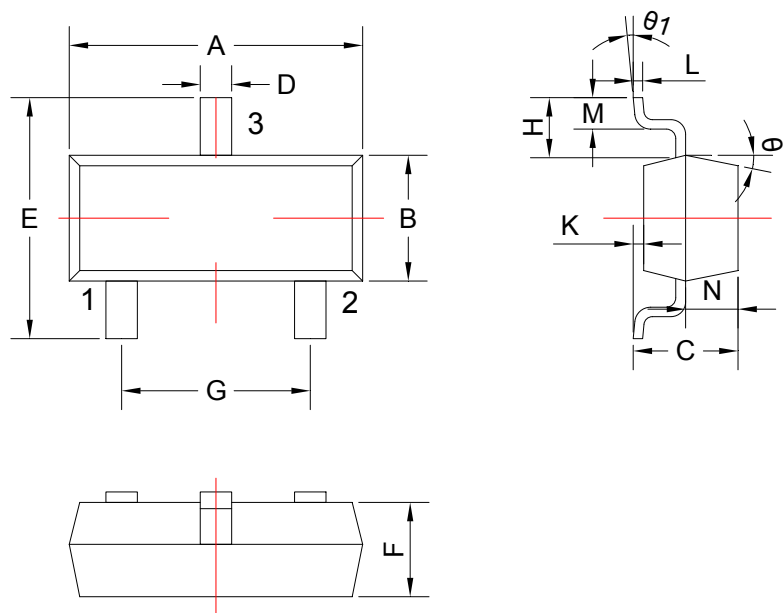


Figure6: Body Diode Characteristics

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8.Dimension (SOT-23)



| COMMON DIMENSIONS CUNITS MEASURE=MILLIMETER |      |      |            |       |       |
|---------------------------------------------|------|------|------------|-------|-------|
| SYMBOL                                      | MIN  | MAX  | SYMBOL     | MIN   | MAX   |
| A                                           | 2.85 | 3.04 | M          | 0.20  | -     |
| B                                           | 1.20 | 1.40 | N          | 0.50  | 0.70  |
| C                                           | 0.90 | 1.10 | $\theta$   | 5°    | 9°    |
| D                                           | 0.40 | 0.50 | F          | 0.95  | 1.05  |
| E                                           | 2.25 | 2.55 | H          | 0.50  | 0.60  |
| G                                           | 1.80 | 2.00 | L          | 0.095 | 0.115 |
| K                                           | 0    | 0.10 | $\theta_1$ | 0°    | 8°    |

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